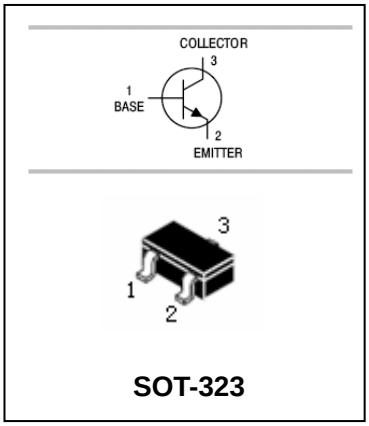
Silicon Epitaxial Planar Transistor **S9018W**

FEATURES

- High current gain bandwidth product.
- power dissipation.(P_C=200mW)

Lead-free



SOT-323

APPLICATIONS

- NPN epitaxial silicon transistor.

ORDERING INFORMATION

Type No.	Marking	Package Code
S9018	J8	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

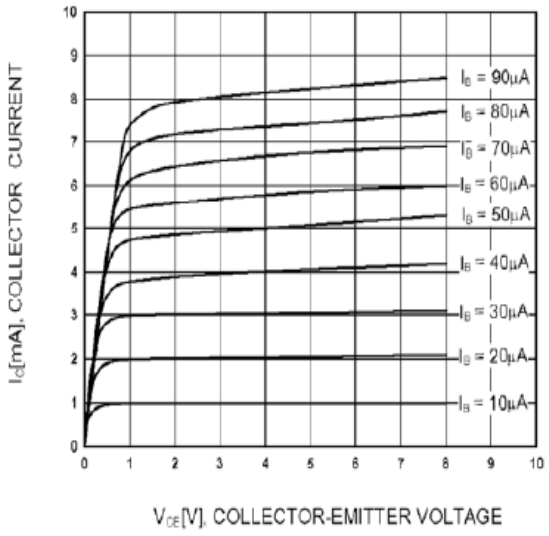
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Dissipation	200	mW
$T_{j,}T_{stg}$	Junction and Storage Temperature	-55~150	℃

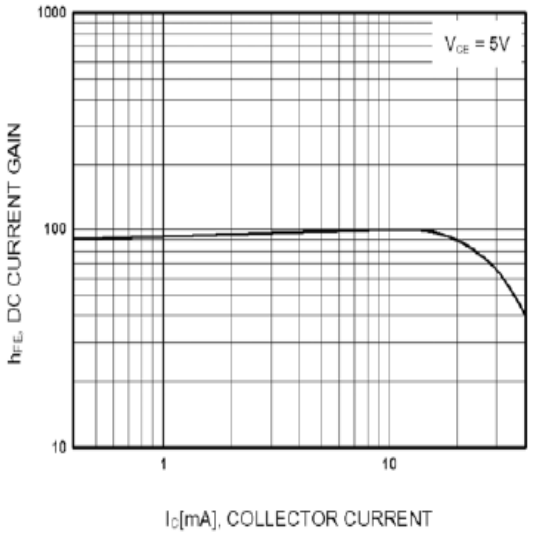
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

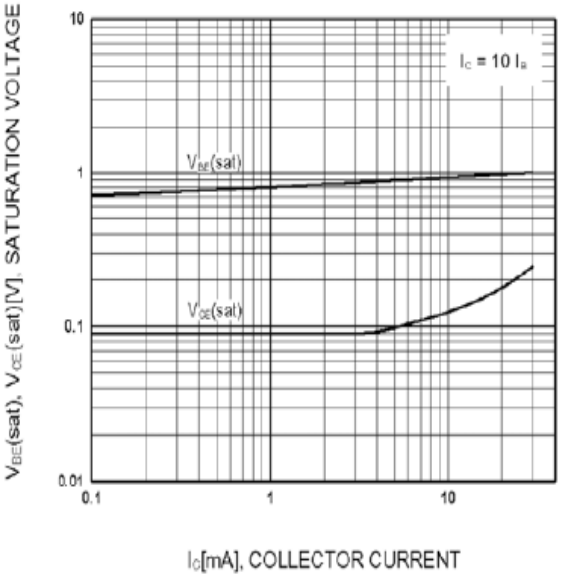
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=0.1mA,I_B=0	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=20V,I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=15V,I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=5V,I_C=1mA	70		190	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10 mA, I_B= 1mA			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=10 mA, I_B= 1mA			1.4	V
Transition frequency	f_T	V_{CE}=5V, I_C= 5mA f=400MHz	600			MHz

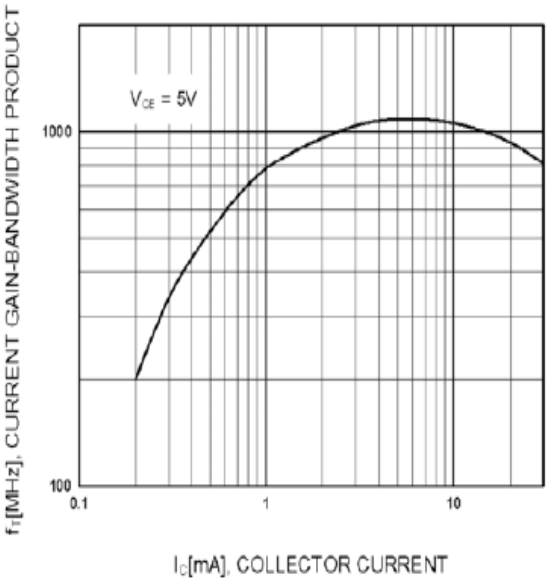
Silicon Epitaxial Planar Transistor **S9018W**

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified





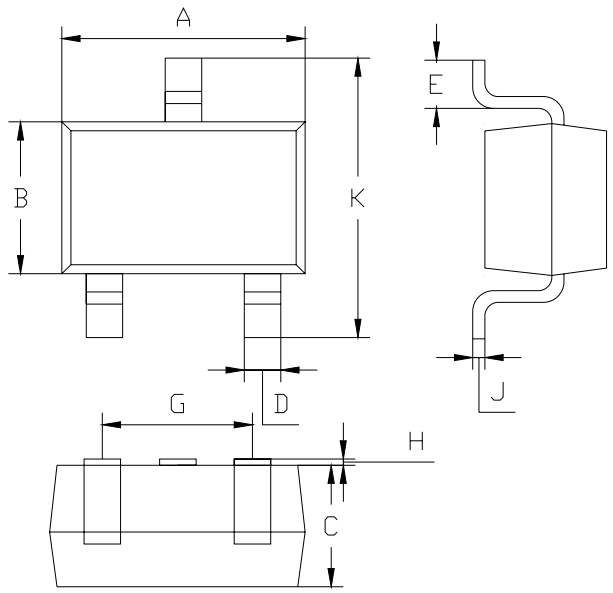




Silicon Epitaxial Planar Transistor **S9018W**

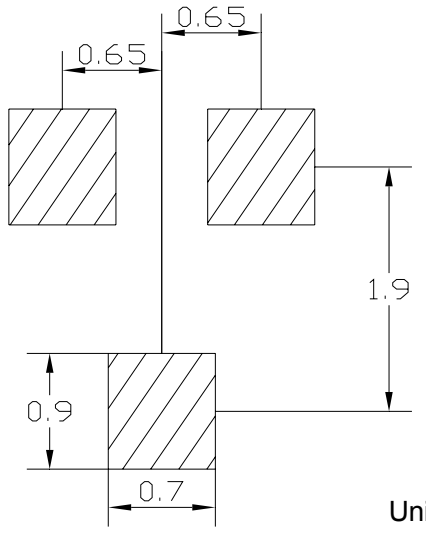
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.1	2.3
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
S9018W	SOT-323	3000/Tape&Reel